

(19) World Intellectual Property  
Organization  
International Bureau



(43) International Publication Date  
26 May 2005 (26.05.2005)

PCT

(10) International Publication Number  
**WO 2005/048277 A1**

(51) International Patent Classification<sup>7</sup>: **H01G 9/025**

(21) International Application Number:

PCT/JP2004/017226

(22) International Filing Date:

12 November 2004 (12.11.2004)

(25) Filing Language:

English

(26) Publication Language:

English

(30) Priority Data:

2003-383211	13 November 2003 (13.11.2003)	JP
60/523,304	20 November 2003 (20.11.2003)	US

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(81) Designated States (*unless otherwise indicated, for every kind of national protection available*): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

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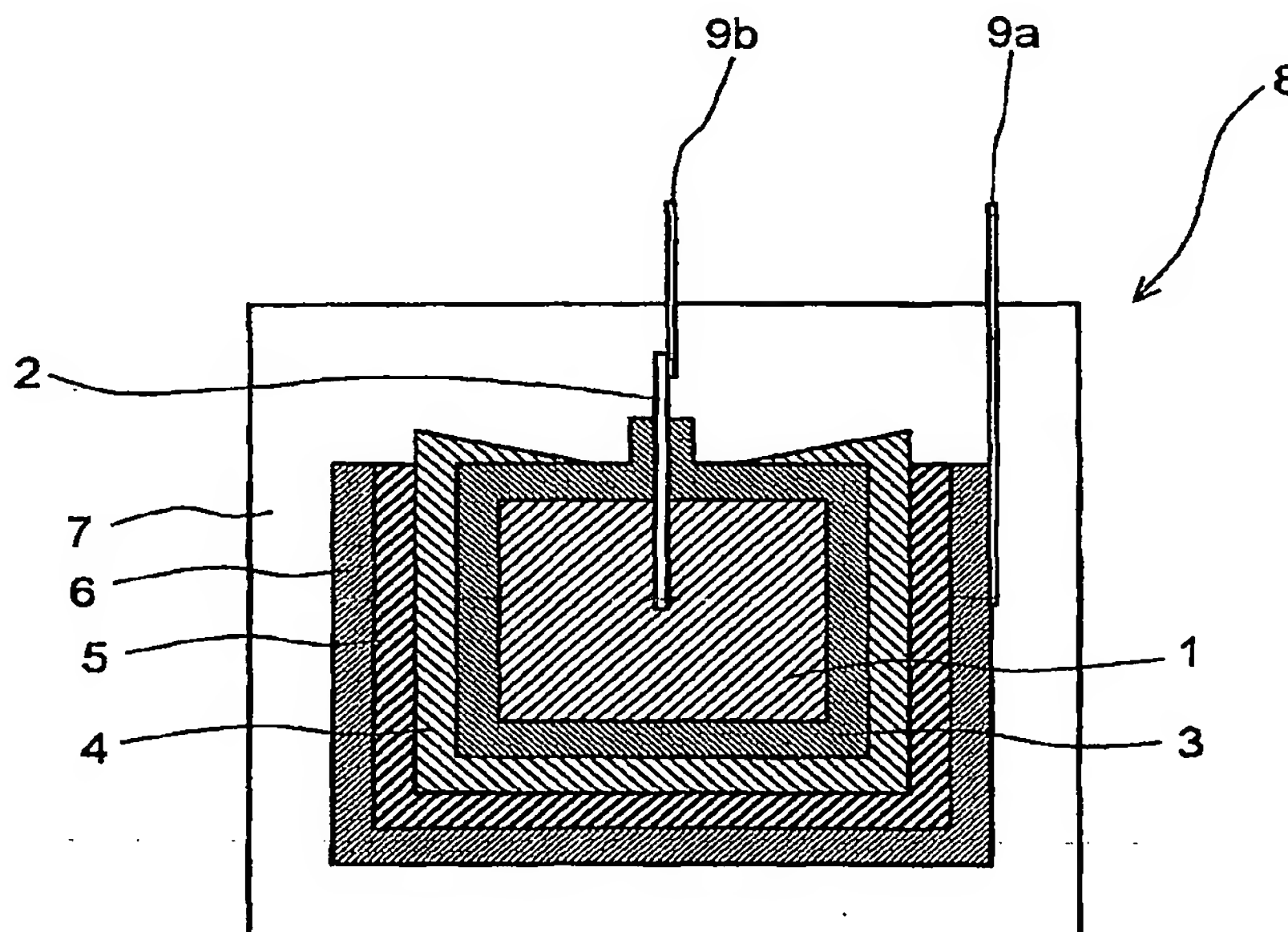
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(84) Designated States (*unless otherwise indicated, for every kind of regional protection available*): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LU, MC, NL, PL, PT, RO, SE,

[Continued on next page]

(54) Title: **SOLID ELECTROLYTE CAPACITOR**



(57) Abstract: The present invention relates to a solid electrolyte capacitor having a small size, a high capacitance, a low ESR and an excellent LC value, which comprises a jacketed capacitor element obtained by sequentially stacking a dielectric oxide film layer, a semiconductor layer and an electrically conducting layer on a surface of a valve-acting metal sintered body or electrically conducting oxide sintered body connected with an anode lead, wherein the thickness of the semiconductor layer in the vicinity of the anode lead-connection point on the sintered body face connected with an anode lead is 5 μm or less, and also relates to an electronic circuit and electronic device using the capacitor.



SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

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**Published:**

— *with international search report*